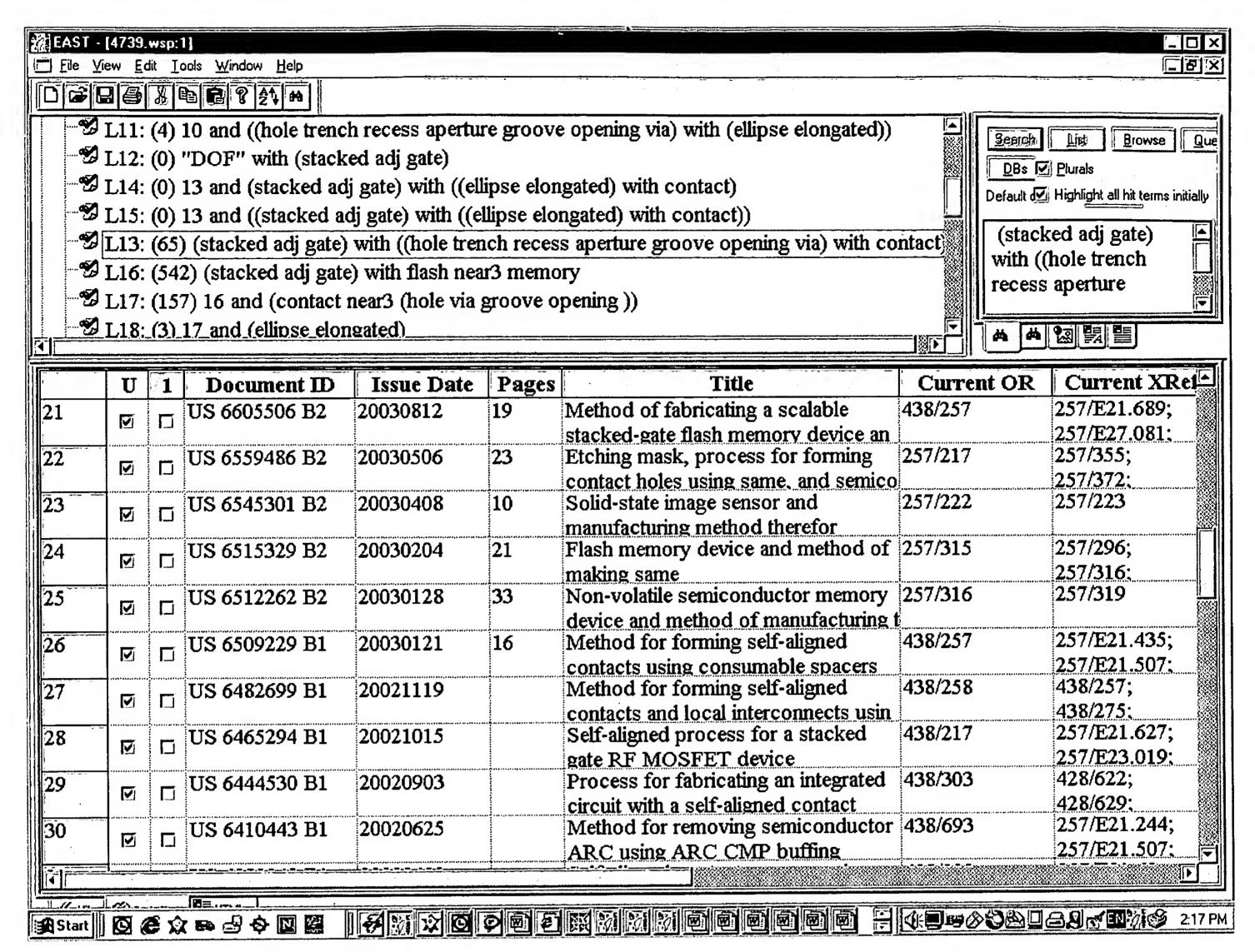
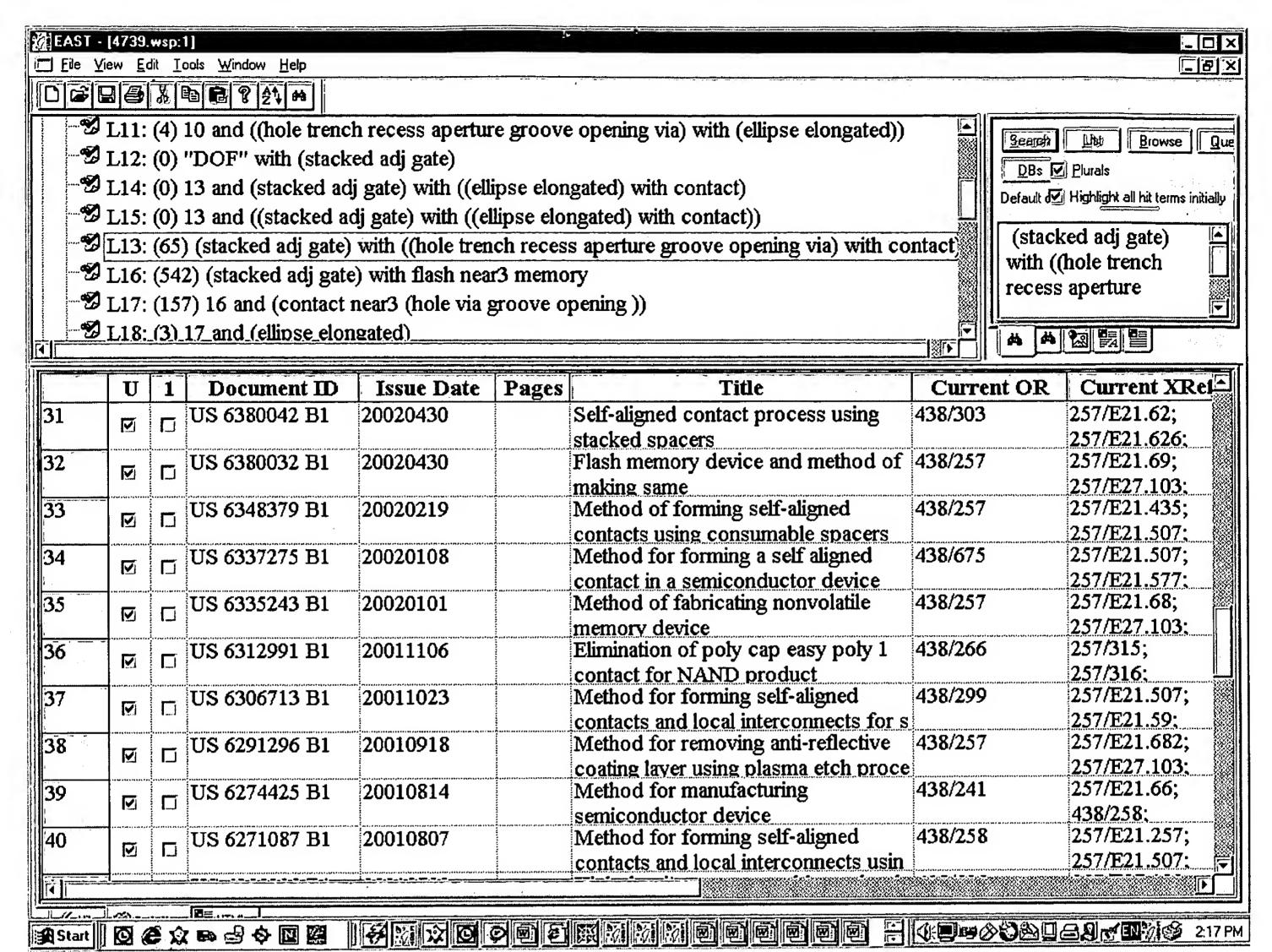
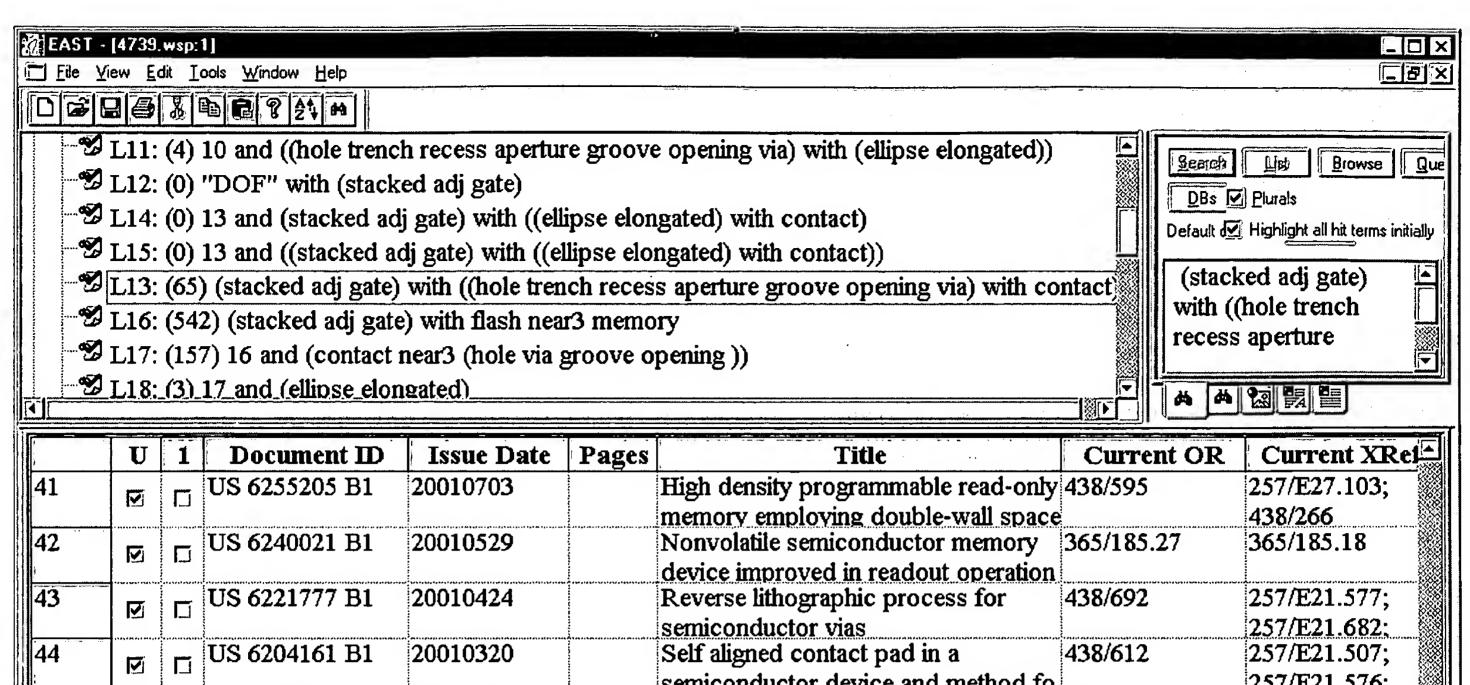


	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRei
11	₽	Г	US 20020072167	20020613	21	Flash memory device and method of	438/201	257/E21.69;
			A1	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		making same	10 M 10 L 10 M 10 L 10 L 10 L 10 L 10 L	257/E27.103;
12	V		US 20020034856	20020321	12	Method for forming junction	438/381	257/E21.166;
			A1			electrode of semiconductor device		257/E21.171:
13		П	US 20020017692	20020214	24	Non-volatile semiconductor memory	ī	257/758;
			A1		<u></u>	device having memory cell array suita		257/E21.682:
14	V		US 20010045585	20011129	35	NON-VOLATILE	257/296	
			A1			SEMICONDUCTOR MEMORY DE		
15		П	US 20010031524	20011018	16	<u> </u>	438/201	257/E21.683;
		<u> </u>	A1			manufacturing method therefor		257/E27.081;
16	V		US 20010015428	20010823	11		257/1	
		ļ	A1		<u> </u>	manufacturing method therefor		
17			US 20010002731	20010607	24		257/750	257/759;
			A1			contact holes using same, and semico		257/760;
18			US 6713388 B2	20040330	12	8	438/673	438/639
<u> </u>						memory device to eliminate charge lo		0.67.7701 1.66
19			US 6667220 B2	20031223	12	Method for forming junction	438/400	257/E21.166;
	3/40					electrode of semiconductor device	400/050	257/E21.171;
20	V		US 6667211 B2	20031223	33	Non-volatile semiconductor memory	,	438/258;
						device and method of manufacturing t	ing the second s	438/589:
1							And the state of t	D







44	Ø		US 6204161 B1	20010320	Self aligned contact pad in a	438/612	257/E21.507;
					semiconductor device and method fo		257/E21.507; 257/E21.576; 257/E21.682;
45 <u>v</u>		Г	US 6190968 B1	20010220	Method for forming EPROM and	438/259	257/E21.682;
					flash memory cells with source-side i	••••••••••••••••••••••••••••••	257/E29.306
46 v			US 6180454 B1	20010130	Method for forming flash memory	438/257	438/266;
	19				devices		438/593
47	V	Г	US 6172395 B1	20010109	Method of manufacture of	257/315	257/346;
			{		self-aligned floating gate, flash memor		257/401;
48	V	П	US 6136649 A	20001024	Method for removing anti-reflective	438/257	257/E21.422;
1	157				coating layer using plasma etch proce	**************************************	257/E21.682;
49	V	П	US 6133096 A	20001017	Process for simultaneously	438/264	257/E21.684;
; }	17.1				fabricating a stack gate flash memory	1 pt. p. c at. a : a an pyr an re : un ayr da r ar an an a : a an a : 11 ar.	257/E27.081;
50	No.		US 6074915 A	20000613	Method of making embedded flash	438/258	257/E21.685;
5		<u> </u>			memory with salicide and sac structur		438/655
		:					<u> </u>

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